

PRODUCTS Semiconductor IC TYPE BA178MXXFP

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STRUCTURE

Silicon Monolithic Integrated Circuit

TYPE

Three-Terminal Regulator

PRODUCT SERIES

BA178MXXFP

FEATURE

Output current up to 0.5A

OABSOLUTE MAXIMUM RATING (Ta=25°C)

Parameter	Symbol	Limit	Unit
Input Voltage	Vin	35	V
Power Dissipation 1	Pd1	1*1	W
Power Dissipation 2	Pd2	10* ²	W
Output Current	lout	0.5* ³	Α
Operating Temperature Range	Topr	-40~+85	ပ
Storage Temperature Range	Tstg	-55~+150	ပ
Maximum Junction Temperature	Tjmax	150	ဇ

^{*1} Derating in done 8mW/°C for temperatures above Ta=25°C.

ORECOMMENDED OPERATING CONDITIONS (Ta=-40~+85°C)

		11110 001101110110																		
Parameter	Symbol	Туре	Min	Max	Unit															
		BA178M05FP	7.5	25																
		BA178M06FP	8.5	21																
		BA178M07FP	9.5	22																
		BA178M08FP	10.5	23																
Input Voltage Vin		BA178M09FP	11.5	24																
	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	Vin	BA178M10FP	12.5	25
		BA178M12FP	15	27																
		BA178M15FP	17.5	30																
					BA178M18FP	21	33													
																BA178M20FP	23	33		
		BA178M24FP	27	33																
Output Current	lo	Common	_	0.5* ³	Α															

The product described in this specification is a strategic product (and/or Service) subject to COCOM regulations.

Status of this document

The Japanese version of this document is the formal specification. A customer may use this translation version only for a reference to help reading the formal version. If there are any differences in translation version of this document, formal version takes priority.

Application example

• ROHM cannot provide adequate confirmation of patents.

The product described in this specification is designed to be used with ordinary electronic equipment or devices (such as audio-visual equipment, office-automation equipment, communications devices, electrical appliances, and electronic toys).

Should you intend to use this product with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, serospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

ROHM assumes no responsibility for use of any circuits described herein, conveys no license under any patent or other right, and makes no representations that the circuits are free from patent infringement.

DESIG	in c	HECK	APPROVAL	DATE:	Apr/22/'05	SPECIFICATION No. : TSZ02201-BA178MXXFP-1-2
Y. T	logo /		Junohashi	REV.	В	ROHM CO., LTD.

^{*2} Derating in done 80mW/°C for temperatures above Ta=25°C, Mounted on infinity Alminium heat sink.

^{*3} Pd, ASO should not be exceeded.

It should not be exported without Authorization from the appropriate government.

This product is not designed for protection against radioactive rays.



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O ELECTRICAL CHARACTERISTICS

 $(Unless \ otherwise \ specified, \ Ta=25^{\circ}C, Vin=10V(05), 11V(06), 13V(07), 14V(08), 15V(09), 16V(10), 19V(12), 23V(15), 27V(18), 29V(20), 33V(24), \ Io=350mA)$

Parameter	Symbol	Туре	Min.	Limit Typ.	Max.	Unit	Condition
		05	4.8	5.0	5.2		
		06	5.75	6.0	6.25]	
		07	6.7	7.0	7.3		
		08	7.7	8.0	8.3]	
		09	8.6	9.0	9.4		
Output Voltage1	Vo1	10	9.6	10.0	10.4	V	I o=350mA
		12	11.5	12.0	12.5]	
		15	14.4	15.0	15.6	1	
		18	17.3	18.0	18.7]	
		20	19.2	20.0	20.8	1	
		24	23.0	24.0	25.0		1
		05	4.75	_	5.25		Vin=7.5~20V, lo=5mA~350mA
		06	5.7	_	6.3]	Vin=8.5~21V, lo=5mA~350mA
	1	07	6.65	_	7.35	1	Vin=9.5~22V, lo=5mA~350mA
		08	7.6	_	8.4	1	Vin=10.5~23V, lo=5mA~350m
		09	8.55		9.45	1	Vin=11.5~24V, lo=5mA~350m
Output Voltage2	Vo2	10	9.5	-	10.5	1 v	Vin=12.5~25V, lo=5mA~350m
-		12	11.4	_	12.6	1	Vin=15~27V, lo=5mA~350mA
		15	14.25		15.75	1	Vin=17.5~30V, lo=5mA~350m
		18	17.1		18.9	1	Vin=21~33V, lo=5mA~350mA
		20	19.0		21.0	1	Vin=23~33V, lo=5mA~350mA
		24	22.8		25.2	1	Vin=27~33V, lo=5mA~350mA
		05		3			Vin=7~25V, lo=200mA
			 		100		
		06		3		1	Vin=8~25V, lo=200mA
		07		4	100	l	Vin=9~25V, lo=200mA
		08		4	100	Į.	Vin=10.5~25V, Io=200mA
	l	09		4	100	mV	Vin=11.5~26V, lo=200mA
Line Regulation1	Reg.I1	10		5	100		Vin=12.5~28V, lo=200mA
		12		5	100		Vin=14.5~30V, lo=200mA
		15		6	100		Vin=17.5~30V, Io=200mA
		18		7	100		Vin=21~33V, lo=200mA
		20		8	100		Vin=23~33V, lo=200mA
		24	-	10	100		Vin=27~33V, lo=200mA
		05		1	50		Vin=8~12V, lo=200mA
		06	_	11	50		Vin=9~25V, lo=200mA
		07	-	1	50		Vin=10~25V, lo=200mA
		08	1	1	50]	Vin=11~25V, Io=200mA
		09	-	2	50		Vin=12~25V, lo=200mA
Line Regulation2	Reg.I2	10	_	2	50	m∨	Vin=14~26V, lo=200mA
-		12	-	3	50		Vin=16~30V, lo=200mA
		15	-	3	50	1	Vin=20~30V, lo=200mA
		18	_	3	50	1	Vin=24~33V, lo=200mA
		20	_	4	50	1	Vin=24~33V, lo=200mA
		24		5	50	1	Vin=28~33V, lo=200mA
		05	62	78	-	-	7 11 20 00 V, 10 20011A
		06	60	74		1	
		07	57	71			
		08	56	69			
		09	56	67		1	
Ripple Rejection	R.R.	10	56	66		dB	ein=1Vrms, f=120Hz,
ppio Nojeotion		12	55	63	_	"	lo=100mA
		15	54	60			
		18	53	58		1	
		20	53	58		1	
		24	50	55		1	
		27					
	 	05	i –	-1.0		i	1
Temperature		05	_	0 F	_	mV/°C	1
Temperature Coefficient of	Tcvo	06/07/08/09/10/12		-0.5		mV/°C	lo=5mA, Tj=0~125°C
•	Tovo	06/07/08/09/10/12 15/18		-0.6	_	mV/°C	lo=5mA, Tj=0~125°C
Coefficient of	Tcvo	06/07/08/09/10/12				mV/°C	lo=5mA, Tj=0~125°C Tj=25°C

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Parameter	Symbol	Туре	Min.	Limit Typ.	Max.	Unit	Condition
		05	- IVIII 1.	20			
				20	100		
		06	 	+			
		07	+	20	140		
		08	 -	20	160		
		09		20	180		
Load Regulation1	Reg.L1	10		20	200	mV	lo=5mA~500mA
		12	_	20	240		1
		15		20	300		
		18	-	20	360		
		20	–	20	400		
		24	-	20	480		
		05	_	10	50		
		06	_	10	60		
		07	_	10	70		
		08		10	80		
		09	 	10	90		
Load Possilation?	Dec 10		 	10	100		lo=5mA~200mA
Load Regulation2	Reg.L2	10	 			mV	IO-SMA~ZUUMA
		12	 	10	120		
		15	 	10	150		
		18		10	180		1
		20		10	200		t
		24	-	10	240		
•		05	_	40	_		
		06	_	60	_		
		07	_	70	1		
	Vn	08	-	80	-		
Output Noise		09	_	90	_		
Voltage		10		100	-	μV	f=10Hz~100kHz
		12	_	110	_		
		15	-	130	_		
		18	-	140	_		
		20		150	_		
		24		170	_		
Bias Current	łb	Common		4.5	6.0	mA	lo=0mA
Bias Current Change 1	lb1	Common	_	-	0.5	mA	lo=5mA~350mA
		05	_		0.8		Vin:8~25V, lo=200mA
		06		_	0.8		Vin:9~25V, lo=200mA
		07			0.8		Vin:10~25V, lo=200mA
		08	_		0.8		Vin:10.5~25V, lo=200mA
		09		-	0.8		Vin:12~25V, lo=200mA
Bias Current Change 2	lb2	10	-	_	0.8	mA	Vin:13~25V, Io=200mA
		12			0.8		Vin:14.5~30V, lo=200mA
		15			8.0		Vin:17.5~30V, lo=200mA
		18	-	-	0.8		Vin:21~33V, lo=200mA
		20			0.8		Vin:23~33V, lo=200mA
Chart Circ. "		24	<u> </u>	-	8.0		Vin:27~33V, Io=200mA
Short-Circuit	los	05/06/07/08		0.4		Α	Vin=25V
Output Current	×,	09/10/12/15/18/20/24		0.17			Vin=30V
		05	 -	9			
		06	<u> </u>	10			
		07	<u> </u>	11			
		08		12			
		09	<u> </u>	13			
Output Resistance	Ro	10	<u> </u>	14		mΩ	f=1kHz
		12	 -	16			
		15		19			
		18	 -	22			
		20	-	25	_		
		24		37			

O Output Voltage and Marking

	·	
Туре	Marking	Output Voltage(V)
BA178M05FP	178M05	5
BA178M06FP	178M06	6
BA178M07FP	178M07	7
BA178M08EP	178M08	8

Туре	Marking	Output Voltage(V)
BA178M09FP	178M09	9
BA178M10FP	178M10	10
BA178M12FP	178M12	12
BA178M15FP	178 M 15	15

Marking	Output Voltage(V)
178M18	18
178 M 20	20
178 M 24	24
	178M18 178M20

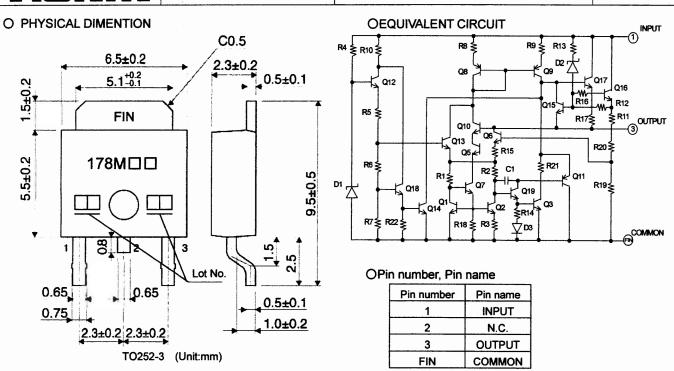
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O NOTES FOR USE

(1) Absolute maximum range

We are careful enough for quality control about this IC. So, there is no problem under normal operation, excluding that it exceeds the absolute maximum ratings. However, Absolute Maximum Ratings are those values beyond which the life of a device may be destroyed we cannot be defined the failure mode, such as short mode or open mode. Therefore physical security countermeasure, like fuse, is to be given when a specific mode to be beyond absolute maximum ratings is considered.

(2) Ground voltage

Make setting of the potential of the GND terminal so that it will be maintained at the minimum in any operating state. Furthermore, check to be sure no terminals are at a potential lower than the GND voltage including an actual electric transient.

(3) Thermal design

When you do the kind of use which exceeds Pd, It may be happened to deteriorating IC original quality such as decrease of electric current ability with chip temperature rise. Do not exceed the power dissipation (Pd) of the package specification rating under actual operation, and please design enough temperature margins.

- (4) Short circuit mode between terminals and wrong mounting
 - Do not mount the IC in the wrong direction and be careful about the reverse-connection of the power connector. Moreover, this IC might be destroyed when the dust short the terminals between them or GND.
- (5) Operation in the strong electromagnetic field

Malfunction may be happened when the device is used in the strong electromagnetic field.

(6) ASO

Do not exceed the maximum ASO and the absolute maximum ratings of the output transistor.

(7) Thermal shutdown circuit

The thermal shutdown circuit (TSD circuit) is built in this product. When IC chip temperature become higher, the thermal shutdown circuit operates and turns output off. The thermal shutdown circuit, which is aimed at isolating the LSI from thermal runaway as much as possible, is not aimed at the protection or guarantee of the LSI. Therefore, do not continuously use the LSI with this circuit operating or use the LSI assuming its operation.

(8) GND wiring pattern

Use separate ground lines for control signals and high current power driver outputs. Because these high current outputs that flows to the wire impedance changes the GND voltage for control signal. Therefore, each ground terminal of IC must be connected at the one point on the set circuit board. As for GND of external parts, it is similar to the above-mentioned.

- (9) Internal circuits could be damaged if there are modes in which the electric potential of the application's input and GND are the opposite of the electric potential of the various outputs. Use of a diode or other such bypass is recommended.
- (10) We recommend to put Diode for protection purpose in case of output pin connected with large load of impedance or reserve current occurred at initial and output off.

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